



P-Channel Enhancement-Mode Vertical DMOS Power FETs

Ordering Information

$BV_{DSS} /$ BV_{DGS}	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	Order Number / Package	
			TO-39	TO-92
-20V	2.0Ω	-2.0A	TP0202N2	TP0202N3
-40V	2.0Ω	-2.0A	TP0204N2	TP0204N3

Features

- ☐ Low threshold
- ☐ High input impedance
- ☐ Low input capacitance
- ☐ Fast switching speeds
- ☐ Low on resistance
- ☐ Freedom from secondary breakdown
- ☐ Low input and output leakage
- ☐ Complementary N- and P-channel devices

Advanced DMOS Technology

These enhancement-mode (normally-off) power transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and negative temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex Vertical DMOS Power FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Applications

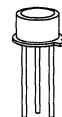
- ☐ Logic level interface
- ☐ Solid state relays
- ☐ Battery operated systems
- ☐ Photo voltaic drive
- ☐ Analog switch
- ☐ General purpose line driver

Ratings and Characteristics

TP02L not recommended for new designs. Refer to TP06L data sheet for all ratings and characteristics.

Package Options

(Note 1)



TO-39



TO-92

Note 1: See Package Outline section for discrete pinouts.